

## Features

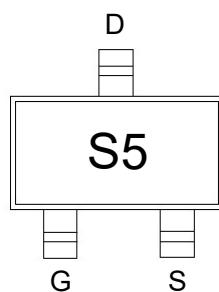
- Leading trench technology for low  $R_{DS(on)}$
- Low Gate Charge

## Product Summary

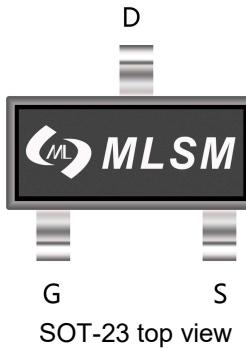
$V_{DS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
-15V	45mΩ@-4.5V	-5A
	60mΩ@-2.5V	

## Application

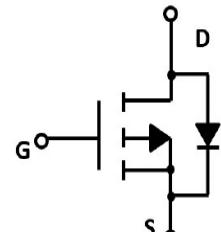
- Video monitor
- Power management



S5: Device code



SOT-23 top view



Schematic diagram



Halogen-Free

Marking and pin assignment

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
--------	-----------	--------	------

## Common Ratings (TC=25°C Unless Otherwise Noted)

$V_{DS}$	Drain-Source Breakdown Voltage	-15	V
$V_{GS}$	Gate-Source Voltage	±10	V
$T_J$	Maximum Junction Temperature	150	°C
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$I_S$	Diode Continuous Forward Current	Tc=25°C -5	A

## Mounted on Large Heat Sink

$I_{DM}$	Pulse Drain Current Tested	Tc=25°C	-18	A
$I_D$	Continuous Drain Current	Tc=25°C	-5	A
$P_D$	Maximum Power Dissipation	Tc=25°C	0.35	W
$R_{QJA}$	Thermal Resistance Junction-to-Ambient		357	°C/W

## Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS2305	SOT-23	S5	3,000	45,000	180,000	7" reel

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
BV <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-15	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V	--	--	-1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.4	-0.6	-1.0	V
R <sub>DS(on)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.5A	--	30	45	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3.0A	--	40	60	mΩ
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-2.0A	--	60	90	mΩ

**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)**

C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1MHz	--	606	--	pF
C <sub>OSS</sub>	Output Capacitance		--	114	--	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		--	103	--	pF

**Switching Characteristics**

Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-10V, I <sub>D</sub> =-3.8A, V <sub>GS</sub> =-10V	--	8.48	--	nC
Q <sub>gs</sub>	Gate Source Charge		--	1.54	--	nC
Q <sub>gd</sub>	Gate Drain Charge		--	2.61	--	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =-10V, I <sub>D</sub> =-3.8A, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =3Ω	--	5.8	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	34.8	--	nS
t <sub>d(off)</sub>	Turn-Off Delay Time		--	51.4	--	nS
t <sub>f</sub>	Turn-Off Fall Time		--	52	--	nS

**Source- Drain Diode Characteristics**

V <sub>SD</sub>	Forward on voltage	T <sub>j</sub> =25°C, I <sub>s</sub> =-4.1A	--	--	-1.2	V
-----------------	--------------------	---	----	----	------	---

### Typical Operating Characteristics

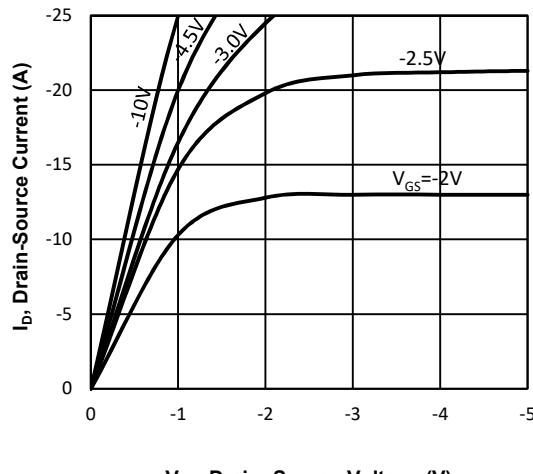


Fig1. Typical Output Characteristics

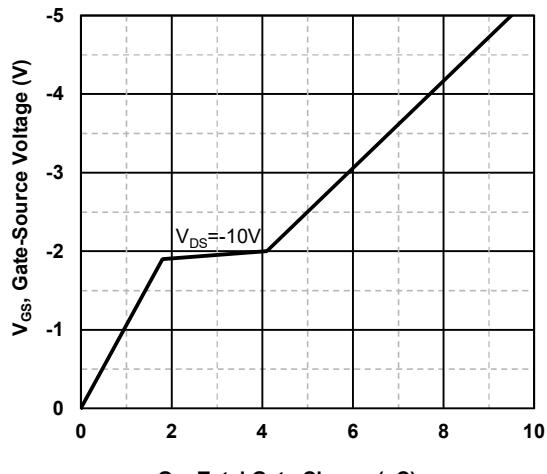


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

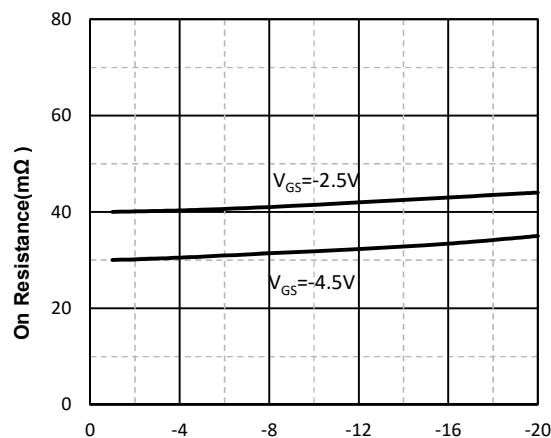


Fig3. Drain-Source on Resistance

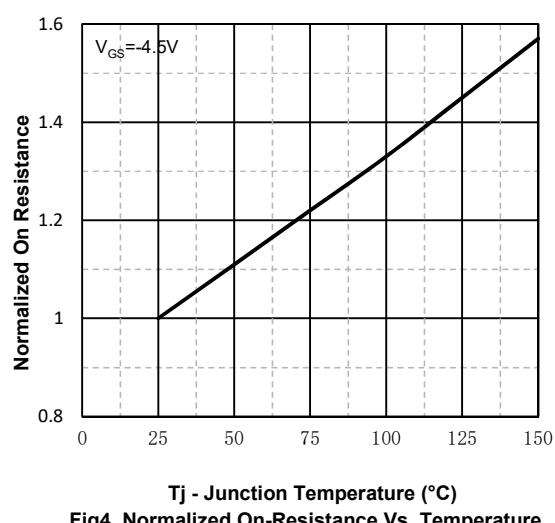


Fig4. Normalized On-Resistance Vs. Temperature

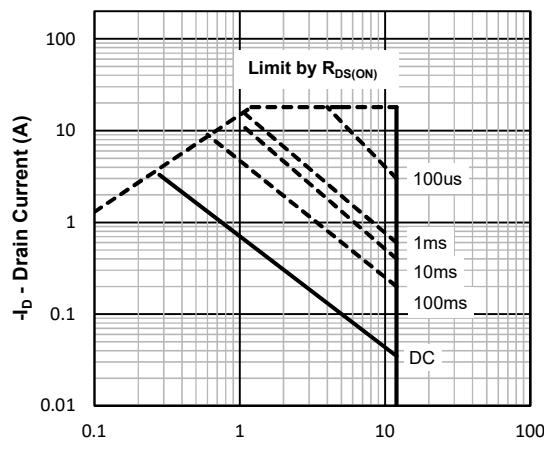


Fig5. Maximum Safe Operating Area

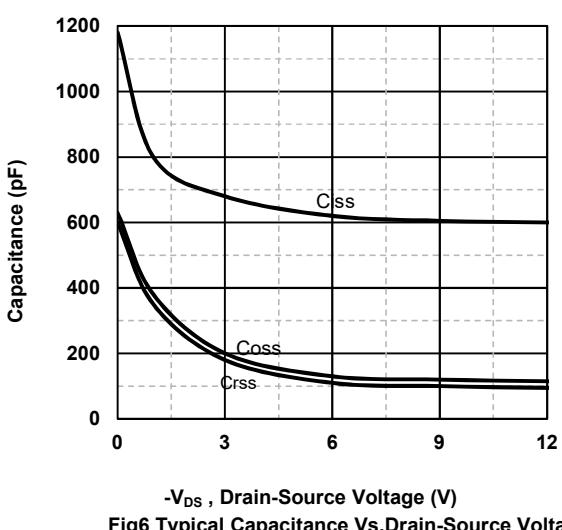
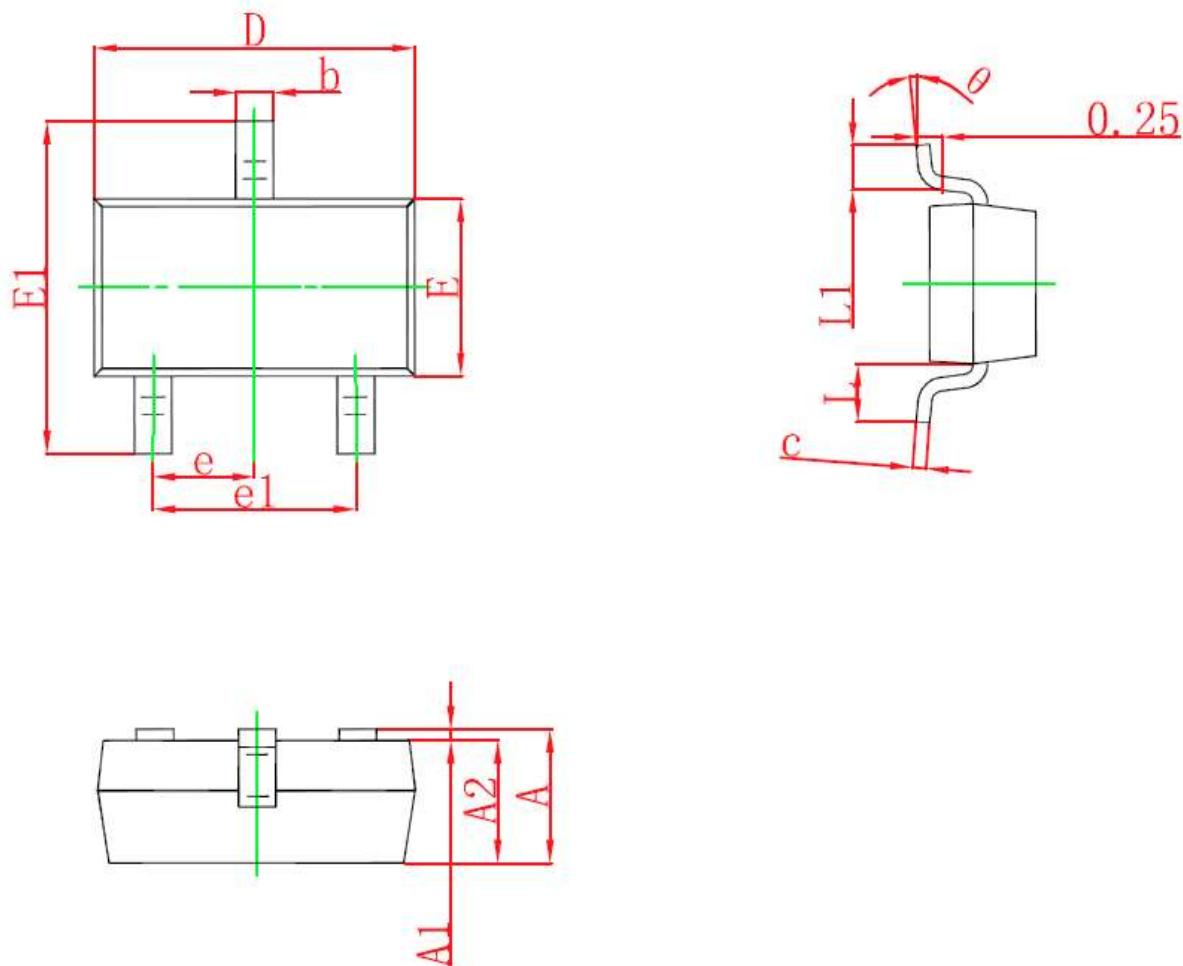


Fig6 Typical Capacitance Vs.Drain-Source Voltage

## SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E1	2.250	2.550	0.088	0.100
E	1.200	1.400	0.047	0.055
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°